



DRD (xxxx) W

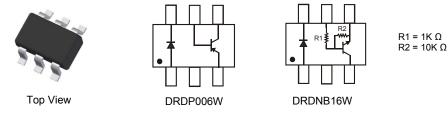
#### **COMPLEX ARRAY FOR RELAY DRIVERS**

#### **Features and Benefits**

- Epitaxial Planar Die Construction
- One Transistor and One Switching Diode in One Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

#### **Mechanical Data**

- Case: SOT-363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Alloy 42 lead-frame. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (approximate)



#### Ordering Information (Note 4)

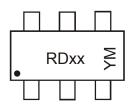
Device	Compliance	Packaging	Shipping
DRDP006W-7	Commercial	SOT-363	3000/Tape & Reel
DRDNB16W-7	Commercial	SOT-363	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



RDxx = Product Type Marking Code: RD02 = DRDP006W RD03 = DRDNB16W YM = Date Code Marking Y = Year (ex: I = 2021) M = Month (ex: 9 = September)

Date Code Key

Year	2005			2021		2022	2023		2024	2025	i	2026
Code	S			-		J	K		L	М		Ν
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings, Total Device @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	200	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{ ext{ heta}JA}$	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

#### Maximum Ratings, DRDP006W PNP Transistor @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current (Note 5)	lc	-600	mA

#### Maximum Ratings, DRDNB16W Pre-Biased NPN Transistor @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V <sub>CC</sub>	50	V
Input Voltage	V <sub>IN</sub>	-5 to +10	V
Output Current	lc	600	mA

### Maximum Ratings, Switching Diode @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage		V <sub>RM</sub>	100	V
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	75	V
RMS Reverse Voltage		V <sub>R(RMS)</sub>	53	V
Forward Continuous Current (Note 5)		I <sub>FM</sub>	500	mA
Average Rectified Output Current (Note 5)		lo	250	mA
Non-Repetitive Peak Forward Surge Current	@ t = 1.0µs @ t = 1.0s	I <sub>FSM</sub>	4.0 1.0	А

Note: 5. Device mounted on FR-4 PCB, 1 inch square 2oz copper pad area.



## Electrical Characteristics, DRDP006W PNP Transistor @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic (Note 6)	Symbol	Min	Тур	Max	Unit	Test Condition
DC Current Gain	h <sub>FE</sub>	—	100	300		I <sub>C</sub> = -150mA, V <sub>CE</sub> = -10V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_		-0.4	V	I <sub>C</sub> = -150mA, I <sub>B</sub> = -15mA
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-60		—	V	$I_{\rm C}$ = -10µA, $I_{\rm E}$ = 0
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-60		—	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-5		—	V	$I_{E} = -10 \mu A$ , $I_{C} = 0$
Collector Cutoff Current	I <sub>CBO</sub>	—		-10	nA	$V_{CB} = -50V, I_E = 0$
Current Gain-Bandwidth Product	f⊤	_	200	_	MHz	V <sub>CE</sub> = -20V, I <sub>C</sub> = -50mA, f = 100MHz
Capacitance	Cobo			8	pF	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f = 1MHz

### Electrical Characteristics, DRDNB16W Pre-Biased NPN Transistor @TA = 25°C unless otherwise specified

Characteristic (Note 6)	Symbol	Min	Тур	Max	Unit	Test Condition
Input Voltage	V <sub>I(off)</sub>	0.3	—	_	V	V <sub>CC</sub> = 5V, I <sub>O</sub> = 100µA
input voltage	V <sub>l(on)</sub>			2.0	V	V <sub>O</sub> = 0.3V, I <sub>O</sub> = 20mA
Output Voltage	V <sub>O(on)</sub>			0.3	V	I <sub>O</sub> /I <sub>I</sub> = 50mA/2.5mA
Input Current	lı lı	_	_	7.2	mA	V <sub>1</sub> = 5V
Output Current	I <sub>O(off)</sub>			0.5	μA	$V_{CC} = 50V, V_1 = 0V$
DC Current Gain	GI	56				V <sub>O</sub> = 5V, I <sub>O</sub> = 50mA
Gain-Bandwidth Product	f⊤		200		MHz	V <sub>CE</sub> = 10V, I <sub>E</sub> = 5mA, f = 100MHz

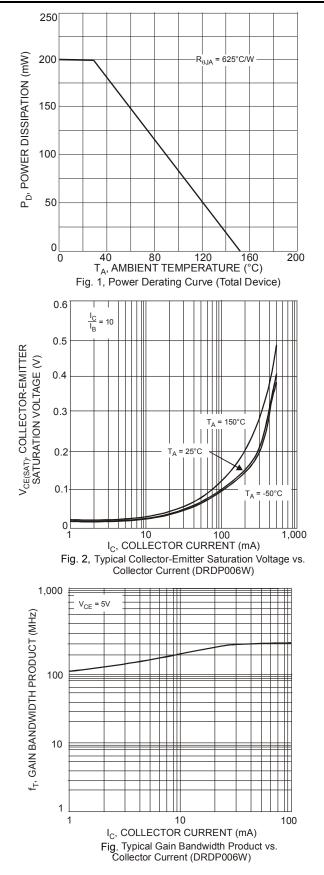
### Electrical Characteristics, Switching Diode @T<sub>A</sub> = 25°C unless otherwise specified

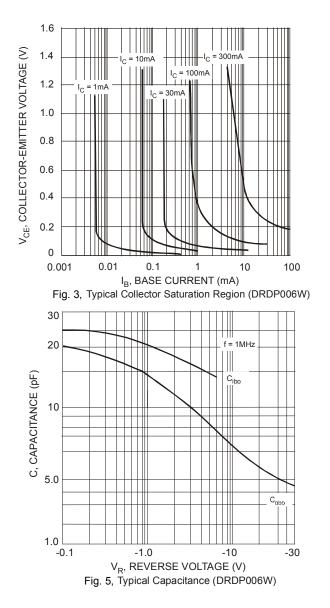
Characteristic	Symbol	Min	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 6)	V <sub>(BR)R</sub>	75	_	_	I <sub>R</sub> = 10μA
Forward Voltage	V <sub>F</sub>	0.62 — — —	0.72 0.855 1.0 1.25	V	I <sub>F</sub> = 5.0mA I <sub>F</sub> = 10mA I <sub>F</sub> = 100mA I <sub>F</sub> = 150mA
Reverse Current (Note 6)	I <sub>R</sub>	_	2.5 50 30 25	μΑ μΑ μΑ nA	V <sub>R</sub> = 75V V <sub>R</sub> = 75V, T <sub>J</sub> = 150°C V <sub>R</sub> = 25V, T <sub>J</sub> = 150°C V <sub>R</sub> = 20V
Total Capacitance	CT		4.0	pF	V <sub>R</sub> = 0, f = 1.0MHz
Reverse Recovery Time	t <sub>rr</sub>	_	4.0	ns	$I_{F} = I_{R} = 10 \text{mA},$ $I_{rr} = 0.1 \times I_{R}, R_{L} = 100 \Omega$

Note: 6. Short duration pulse test used to minimize self-heating effect.



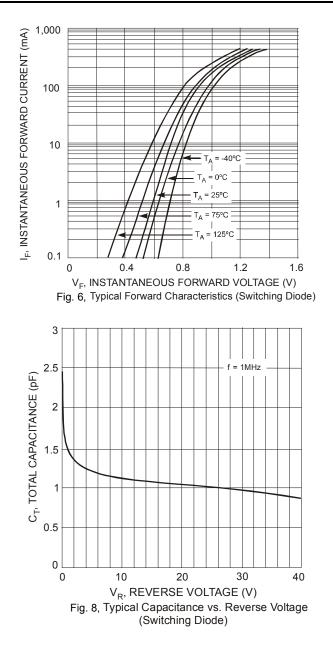
### **Device Characteristics**

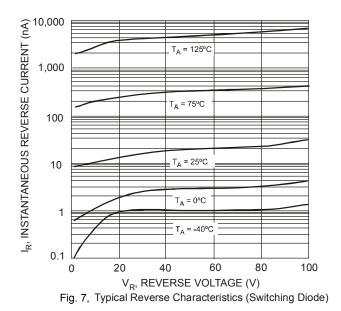






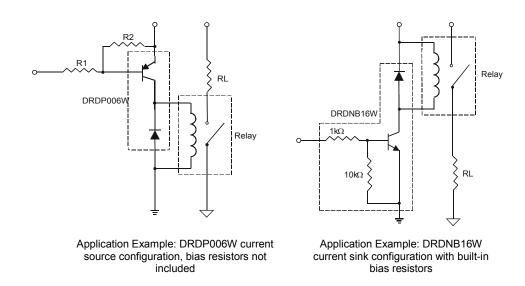
## Device Characteristics (continued)







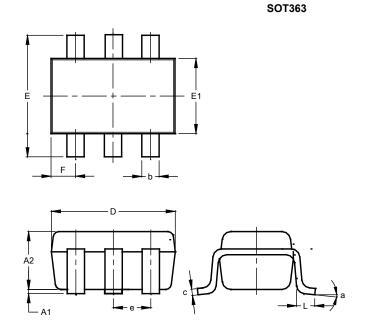
# Sample Applications





### **Package Outline Dimensions**

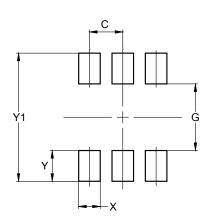
Please see http://www.diodes.com/package-outlines.html for the latest version.



-									
	SOT363								
Dim	Min	Max	Тур						
A1	0.00	0.10	0.05						
A2	0.90	1.00	0.95						
b	0.10	0.30	0.25						
С	0.10	0.22	0.11						
D	1.80	2.20	2.15						
Е	2.00	2.20	2.10						
E1	1.15	1.35	1.30						
е	C	).650 E	SC						
F	0.40	0.45	0.425						
L	0.25	0.40	0.30						
а	0°	8°							
All I	Dimen	sions	in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Y	0.600
Y1	2.500

SOT363



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